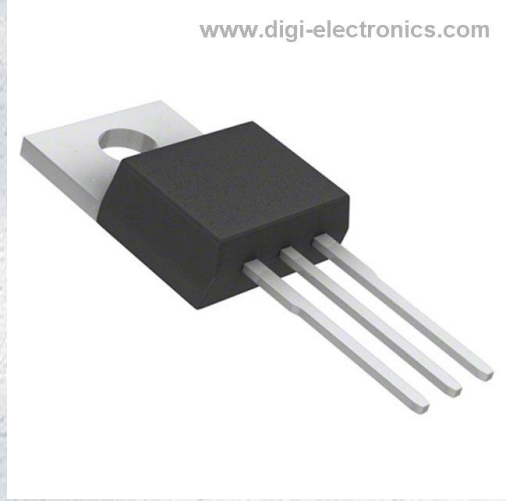
FDP80N06 Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number	FDP80N06-DG
Manufacturer	onsemi
Manufacturer Product Number	FDP80N06
Description	MOSFET N-CH 60V 80A TO220-3
Detailed Description	N-Channel 60 V 80A (Tc) 176W (Tc) Through Hole TO-220-3

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
FDP80N06	onsemi
Series:	Product Status:
UniFET™	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
60 V	80A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
10V	10mOhm @ 40A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
4V @ 250µA	74 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	3190 pF @ 25 V
FET Feature:	Power Dissipation (Max):
-	176W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 175°C (TJ)	Through Hole
Supplier Device Package:	Package / Case:
TO-220-3	TO-220-3
Base Product Number:	
FDP80	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	Not Applicable
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

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FAIRCHILD SEMICONDUCTOR®

November 2013

FDP80N06

N-Channel UniFET™ MOSFET

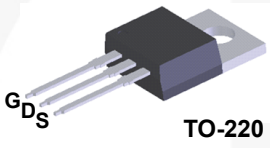
60 V, 80 A, 10 mΩ

Features

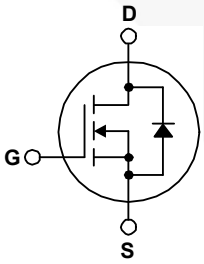
- $R_{DS(on)}$ = 8.5 mΩ (Typ.) @ V_{GS} = 10 V, I_D = 40 A
- Low Gate Charge (Typ. 57nC)
- Low C_{rss} (Typ. 145pF)
- Fast Switching
- Improved dv/dt Capability
- RoHS Compliant

Description

UniFET™ MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



TO-220



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted.

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain to Source Voltage		60	V
V_{GSS}	Gate to Source Voltage		±20	V
I_D	Drain Current	- Continuous (T_C = 25°C)	80	A
		- Continuous (T_C = 100°C)	65	
I_{DM}	Drain Current	- Pulsed (Note 1)	320	A
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	480	mJ
I_{AR}	Avalanche Current	(Note 1)	80	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	17.6	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns
P_D	Power Dissipation	(T_C = 25°C)	176	W
		- Derate above 25°C	1.17	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	°C
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

Thermal Characteristics

Symbol	Parameter	Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.85	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP80N06	FDP80N06	TO-220	Tube	N/A	50 units

Electrical Characteristics

TC = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V, T_J = 25°C	60	-	-	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250μA, Referenced to 25°C	-	0.075	-	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 60V, V_{GS} = 0V	-	-	1	μA
		V_{DS} = 48V, T_C = 150°C	-	-	10	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±20V, V_{DS} = 0V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10V, I_D = 40A	-	8.5	10	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 25V, I_D = 40A	-	67	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V f = 1MHz	-	2450	3190	pF
C_{oss}	Output Capacitance		-	910	1190	pF
C_{rss}	Reverse Transfer Capacitance		-	145	190	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 30V, I_D = 80A R_G = 25Ω	-	32	75	ns
t_r	Turn-On Rise Time		-	259	528	ns
$t_{d(off)}$	Turn-Off Delay Time		-	136	282	ns
t_f	Turn-Off Fall Time	(Note 4)	-	113	236	ns
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{DS} = 48V, I_D = 80A V_{GS} = 10V	-	57	74	nC
Q_{gs}	Gate to Source Gate Charge		-	15	-	nC
Q_{gd}	Gate to Drain “Miller” Charge	(Note 4)	-	24	-	nC
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	80	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	320	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_{SD} = 80A	-	-	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0V, I_{SD} = 80A dI_F/dt = 100A/μs	-	64	-	ns
Q_{rr}	Reverse Recovery Charge		-	127	-	nC

Notes:
1: Repetitive Rating: Pulse width limited by maximum junction temperature.
2: L = 0.15mH, I_{AS} = 80A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C.
3: I_{SD} ≤ 80A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C.
4: Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

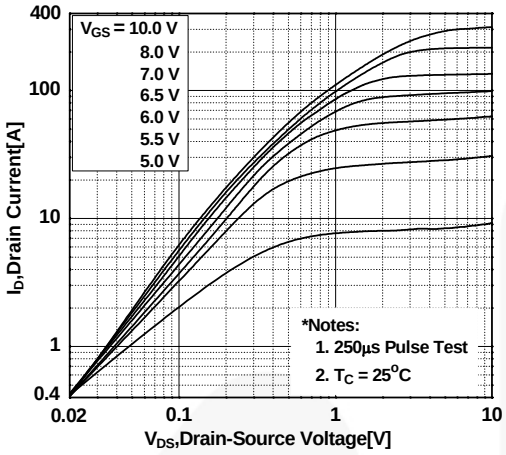


Figure 2. Transfer Characteristics

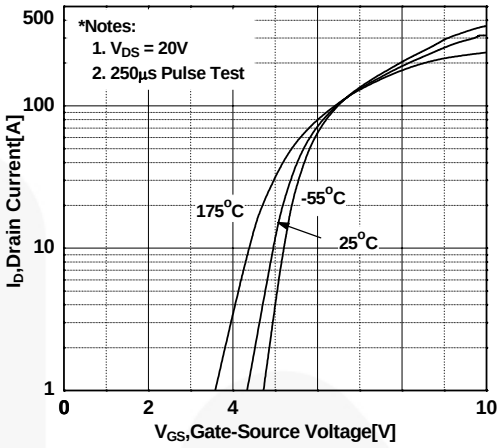


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

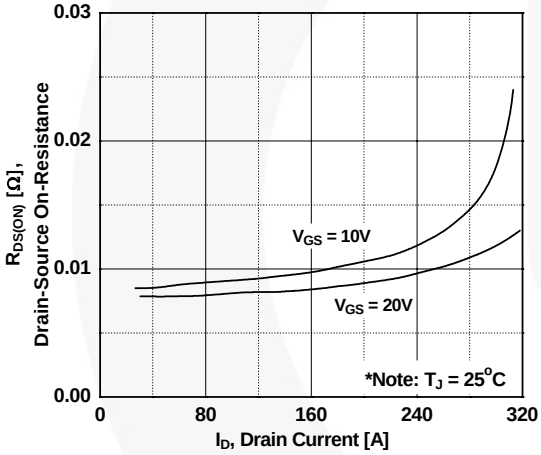


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

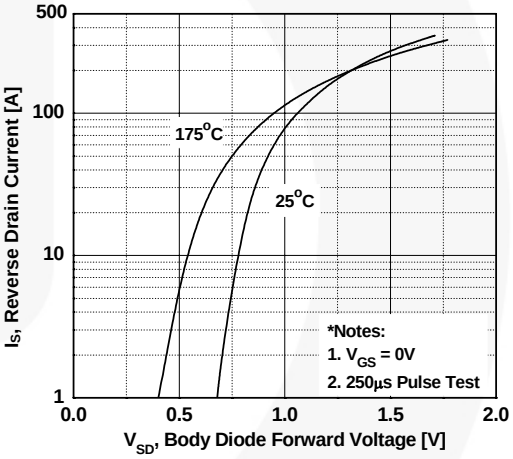


Figure 5. Capacitance Characteristics

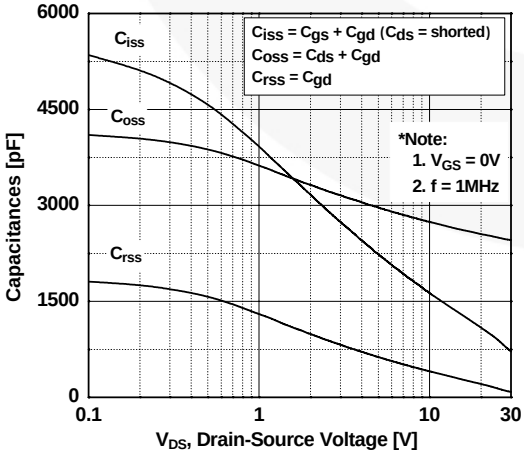
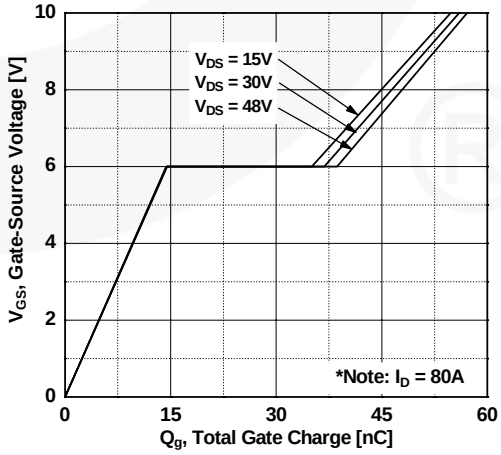


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

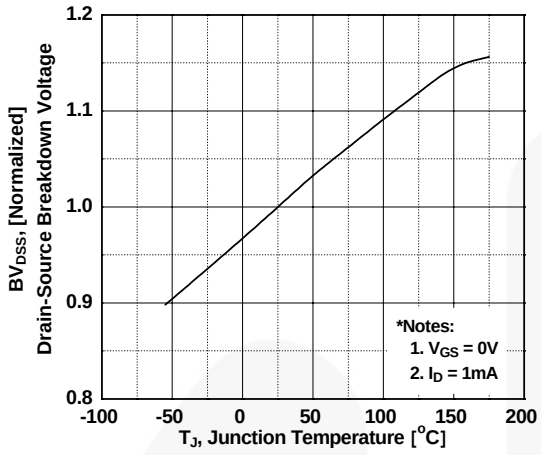


Figure 8. On-Resistance Variation vs. Temperature

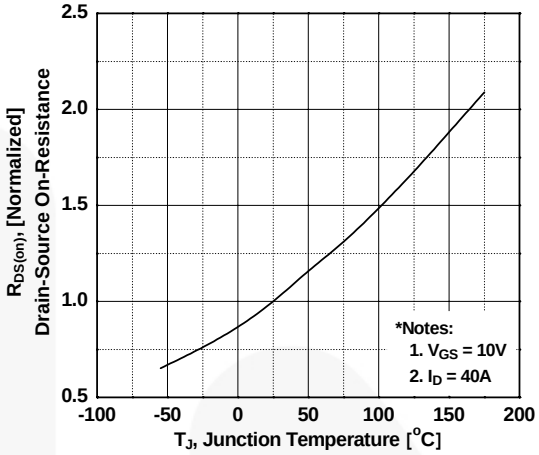


Figure 9. Maximum Safe Operating Area

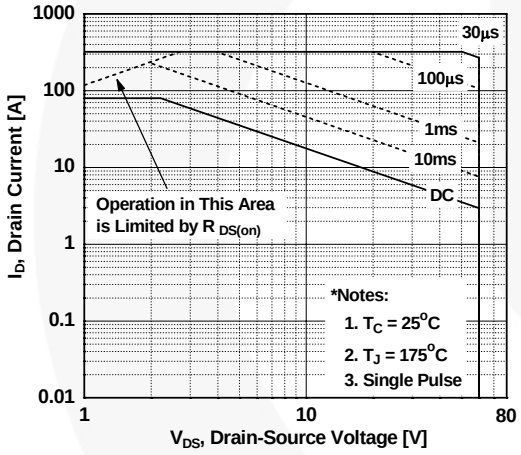


Figure 10. Maximum Drain Current vs. Case Temperature

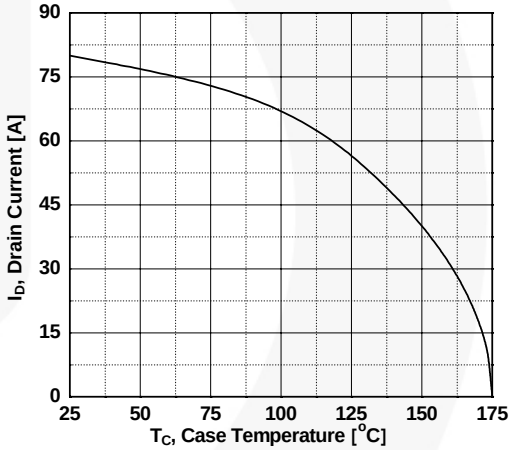


Figure 11. Transient Thermal Response Curve

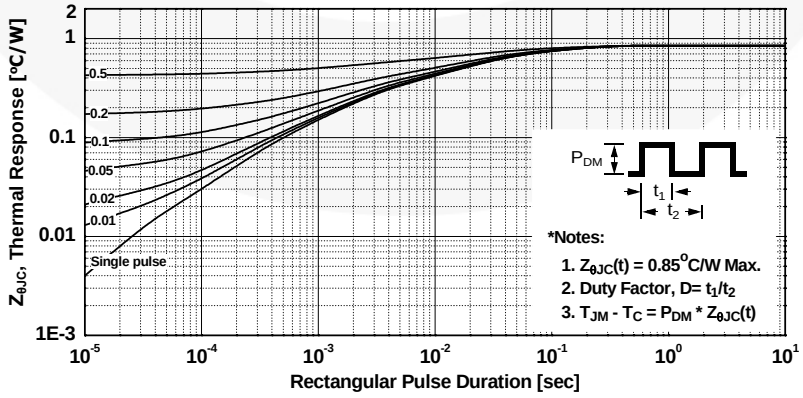


Figure 12. Gate Charge Test Circuit & Waveform

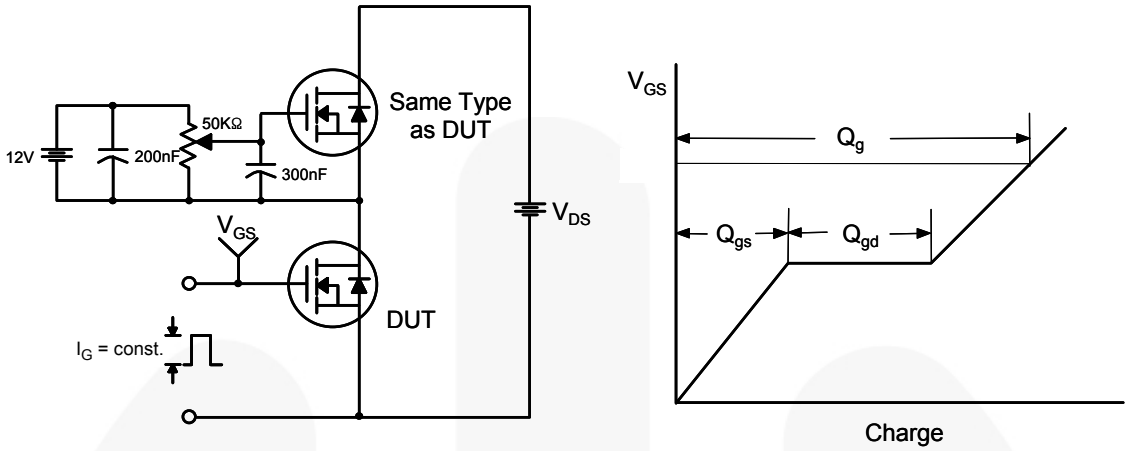


Figure 13. Resistive Switching Test Circuit & Waveforms

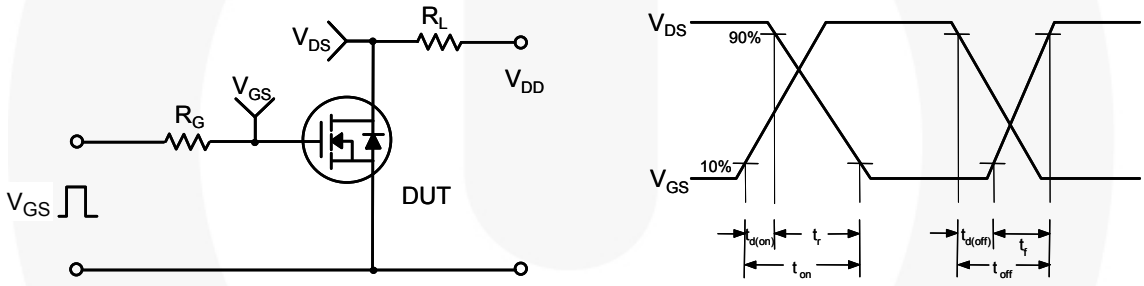


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

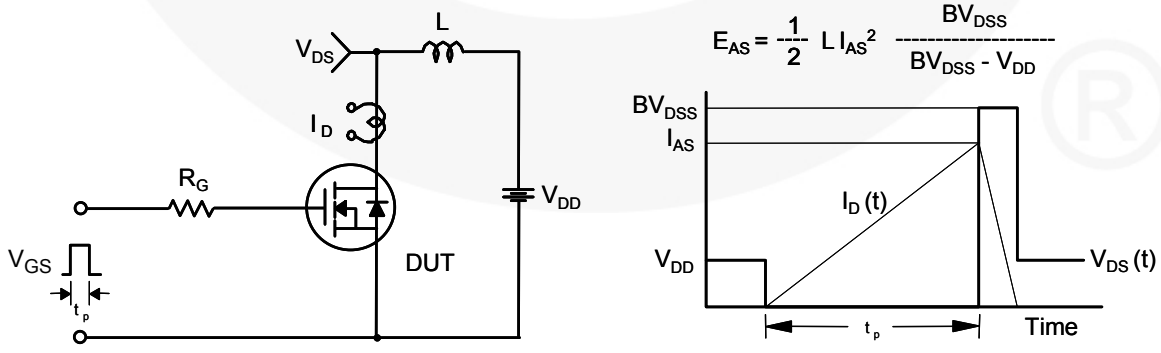
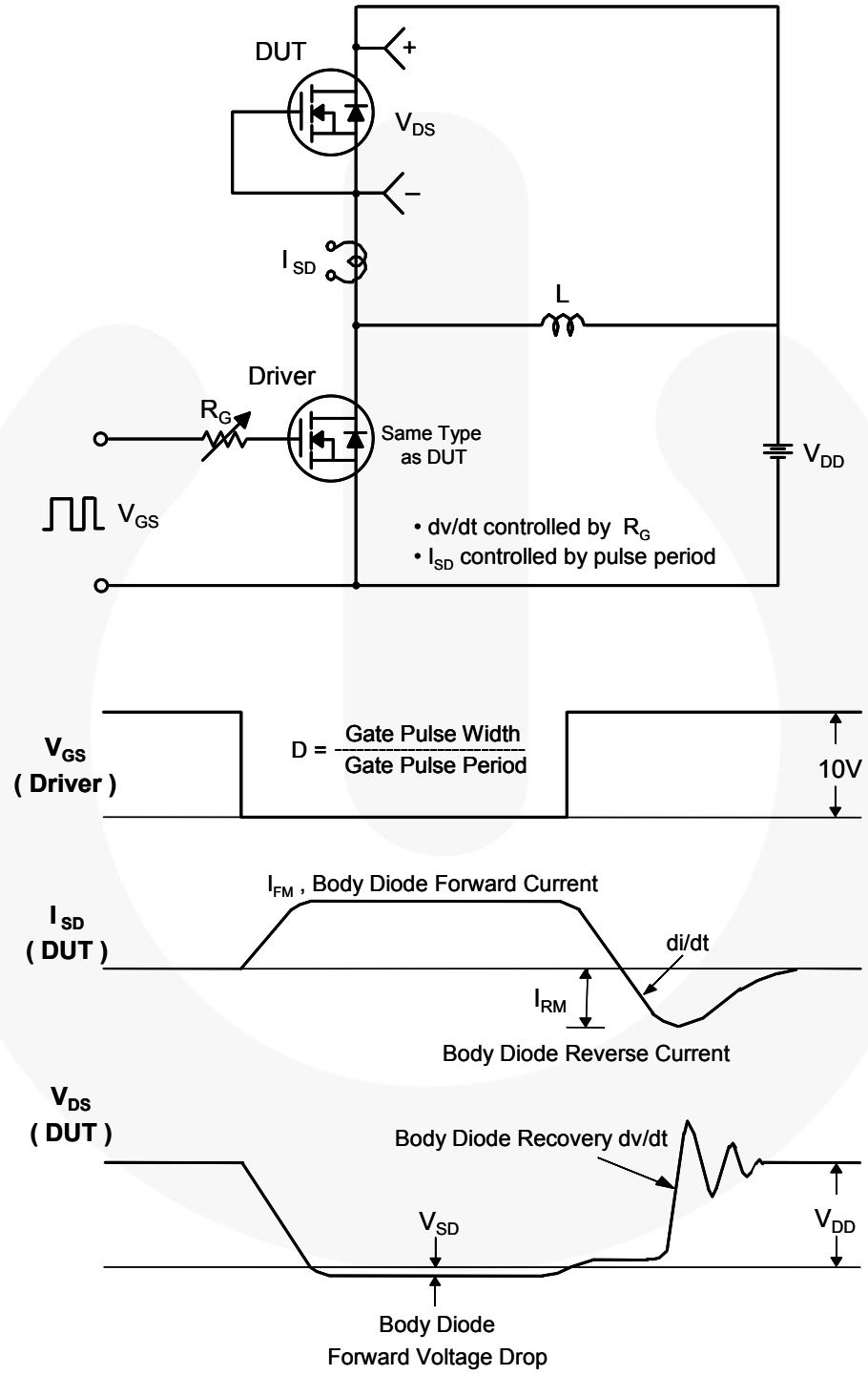


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

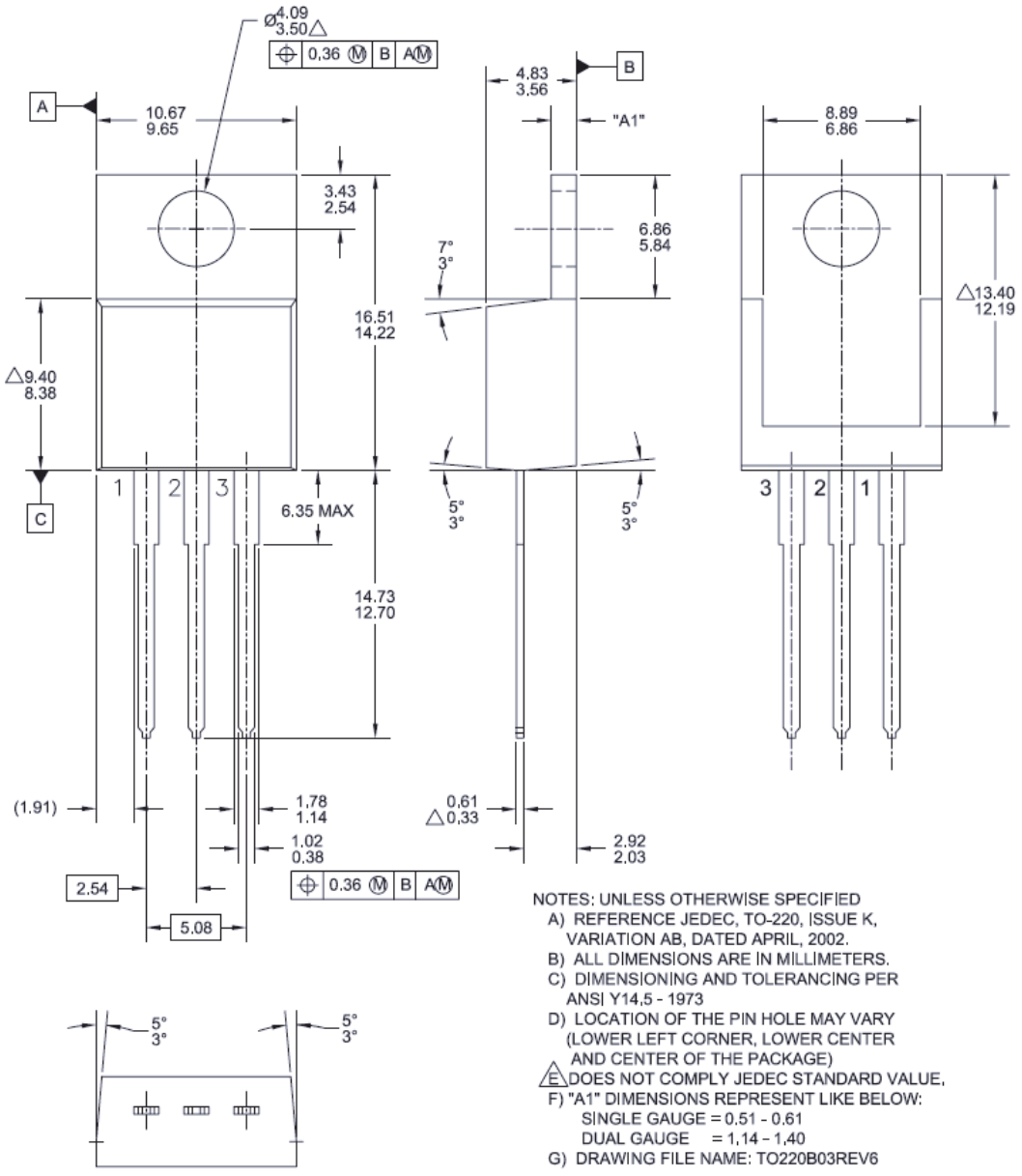


Figure 16. TO-220, Molded, 3Lead, Jedec Variation AB

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No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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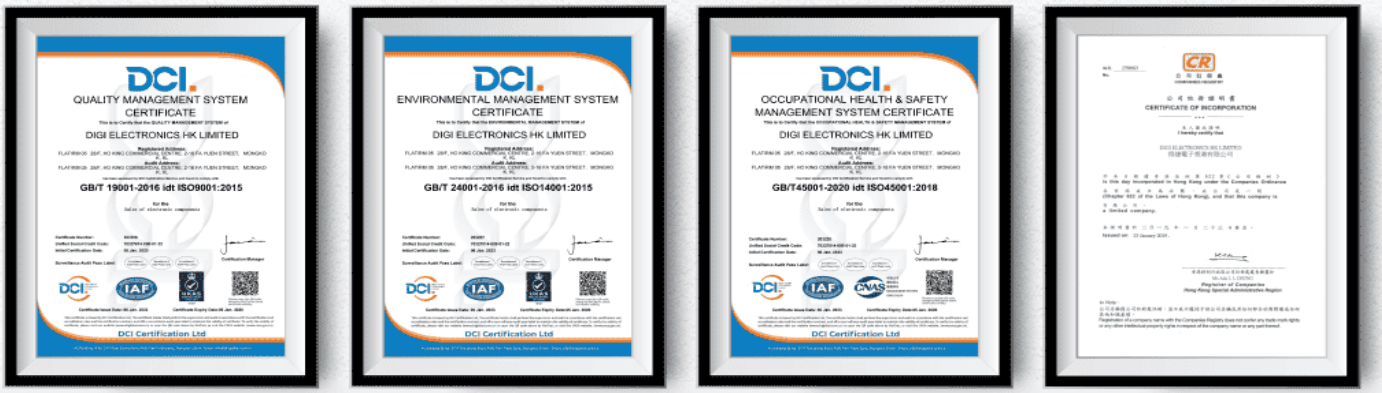

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